

IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended): A polishing pad for a semiconductor wafer, which comprises a substrate for a polishing pad provided with a through hole penetrating from surface to back, and a light transmitting part fitted in said through hole,

wherein said light transmitting part comprises a water-insoluble matrix material and a water-soluble particle dispersed in said water-insoluble matrix material, ~~and~~

wherein a content of said water-soluble particle is not less than ~~0.1%~~ 0.5% by volume and less than 5% by volume based on 100% by volume of the total amount of said water-insoluble matrix material and said water-soluble particle, and

wherein a thickness of said light transmitting part is from 0.1 mm to 3 mm.

Claim 2 (Original): The polishing pad for a semiconductor wafer according to Claim 1, wherein at least a part of the water-insoluble matrix material is a crosslinked polymer.

Claim 3 (Original): The polishing pad for a semiconductor wafer according to Claim 2, wherein said crosslinked polymer is crosslinked 1,2-polybutadiene.

Claim 4 (Original): The polishing pad for a semiconductor wafer according to Claim 1, wherein said light transmitting part is thinned.

Claim 5 (Original): The polishing pad for a semiconductor wafer according to Claim 1, wherein a light transmittance of said light transmitting part at a wavelength between 400 and 800nm is 0.1% or more, or an integrated transmittance of said light transmitting part in a

wavelength range between 400 and 800nm is 0.1% or more, when a thickness of said light transmitting part is 2mm.

Claim 6 (Currently Amended): A polishing pad for a semiconductor wafer, which comprises a substrate for a polishing pad provided with a through hole penetrating from surface to back, a light transmitting part fitted in said through hole, and a fixing layer formed on a backside of at least said substrate for a polishing pad among said substrate for a polishing pad and said light transmitting part for fixing to a polishing apparatus,

wherein said light transmitting part comprises a water-insoluble matrix material and a water-soluble particle dispersed in said water-insoluble matrix material, and

wherein a content of said water-soluble particle is ~~0.1 to 90%~~ 0.5 to 5% by volume based on 100% by volume of the total amount of said water-insoluble matrix material and said water-soluble particle, and

wherein a thickness of said light transmitting part is from 0.1 mm to 3 mm.

Claim 7 (Previously Presented): A laminated body for polishing of a semiconductor wafer, which comprises a polishing pad for a semiconductor wafer as defined in claim 1, and a supporting layer laminated on a backside of said polishing pad for a semiconductor wafer, wherein said laminate body has light transmitting properties in a laminated direction.

Claim 8 (Currently Amended): A laminated body for polishing of a semiconductor wafer, which comprises a substrate for a polishing pad provided with a through hole penetrating from surface to back, a light transmitting part fitted in said through hole, a supporting layer laminated on a backside of at least said substrate for a polishing pad among

said substrate for a polishing pad and said light transmitting part, and a fixing layer formed on a backside of said supporting layer for fixing to a polishing apparatus,

wherein said light transmitting part comprises a water-insoluble matrix material and a water-soluble particle dispersed in said water-insoluble matrix material, ~~and~~

wherein a content of said water-soluble particle is ~~0.1 to 90%~~ 0.5 to 5% by volume based on 100% by volume of the total amount of said water-insoluble matrix material and said water-soluble particle, and

wherein a thickness of said light transmitting part is from 0.1 mm to 3 mm.

Claim 9 (Previously Presented): A method for polishing a semiconductor wafer using a polishing pad for a semiconductor wafer as defined in claim 1, which comprises a process of detecting a polishing endpoint by the use of an optical endpoint detecting apparatus.

Claim 10 (Previously Presented): A method for polishing a semiconductor wafer using a laminated body for polishing of a semiconductor wafer, which comprises a polishing pad for a semiconductor wafer as defined in claim 1, and a supporting layer laminated on a backside of said polishing pad for a semiconductor wafer, wherein said laminated body has light transmitting properties in a laminated direction, and which comprises a process of detecting a polishing endpoint by the use of an optical endpoint detecting apparatus.

Claim 11 (Previously Presented): The polishing pad for a semiconductor wafer according to Claim 1,

wherein said polishing pad comprises a fixing layer formed on a backside of at least the substrate for a polishing pad among the substrate for a polishing pad and the light transmitting part for fixing to a polishing apparatus, and

wherein said polishing pad has said through hole at a site corresponding to a light transmitting part of the fixing layer.

Claim 12 (Previously Presented): The polishing pad for a semiconductor wafer according to Claim 6, wherein said polishing pad has said through hole at a site corresponding to a light transmitting part of the fixing layer.

Claim 13 (Previously Presented): A laminated body for polishing of a semiconductor wafer, which comprises a polishing pad for a semiconductor wafer as defined in claim 6, and a supporting layer laminated on a backside of said polishing pad for a semiconductor wafer, wherein said laminated body has light transmitting properties in a laminated direction.

Claim 14 (Previously Presented): The laminated body for polishing of a semiconductor wafer according to Claim 8, wherein said polishing pad has said through hole at a site corresponding to a light transmitting part of the fixing layer.

Claim 15 (Previously Presented): A method for polishing a semiconductor wafer using a polishing pad for a semiconductor wafer as defined in claim 6, which comprises a process of detecting a polishing endpoint by the use of an optical endpoint detecting apparatus.

Claim 16 (Previously Presented): A method for polishing a semiconductor wafer using a laminated body for polishing of a semiconductor wafer, which comprises a polishing pad for a semiconductor wafer as defined in claim 6, and a supporting layer laminated on a backside of said polishing pad for a semiconductor wafer, wherein said laminated body has

light transmitting properties in a laminated direction, which comprises a process of detecting a polishing endpoint by the use of an optical endpoint detecting apparatus.

Claim 17 (Previously resented): A method for polishing a semiconductor wafer using a laminated body for polishing of a semiconductor wafer as defined in claim 8, which comprises a process of detecting a polishing endpoint by the use of an optical endpoint detecting apparatus.

Claim 18 (New): A polishing pad for a semiconductor wafer, which comprises a substrate for a polishing pad provided with a through hole penetrating from surface to back, and a light transmitting part fitted in said through hole,

wherein the substrate and the light transmitting part comprise a water-insoluble matrix material and a water-soluble particle dispersed in the water-insoluble matrix material,

wherein the water-insoluble matrix material and the water-soluble particle in the substrate and the light transmitting part are the same,

wherein the content of the water-soluble particle in the light transmitting part and the substrate is not the same, the content of the water-soluble particle in the light transmitting part is not less than 0.5% by volume and less than 5% by volume, and the content of the water-soluble particle in the substrate is from 20% by volume to 90% by volume, wherein % by volume is based on 100% by volume of the total amount of the water-insoluble matrix material and the water-soluble particle in the light transmitting part and the substrate, respectively.

Claim 19 (New): The polishing pad for a semiconductor wafer according to Claim 18, wherein a thickness of said light transmitting part is from 0.1 mm to 3 mm.

Claim 20 (New): The polishing pad for a semiconductor wafer according to Claim 18, wherein at least a part of the water-insoluble matrix material is a crosslinked polymer.

Claim 21 (New): The polishing pad for a semiconductor wafer according to Claim 20, wherein said crosslinked polymer is crosslinked 1,2-polybutadiene.

Claim 22 (New): The polishing pad for a semiconductor wafer according to Claim 18, wherein said light transmitting part is thinned.

Claim 23 (New): The polishing pad for a semiconductor wafer according to Claim 18, wherein a light transmittance of said light transmitting part at a wavelength between 400 and 800nm is 0.1% or more, or an integrated transmittance of said light transmitting part in a wavelength range between 400 and 800nm is 0.1% or more, when a thickness of said light transmitting part is 2mm.

Claim 24 (New): A laminated body for polishing of a semiconductor wafer, which comprises a polishing pad for a semiconductor wafer as defined in Claim 18, and a supporting layer laminated on a backside of said polishing pad for a semiconductor wafer, wherein said laminate body has light transmitting properties in a laminated direction.

Claim 25 (New): A method for polishing a semiconductor wafer using a polishing pad for a semiconductor wafer as defined in Claim 18, which comprises a process of detecting a polishing endpoint by the use of an optical endpoint detecting apparatus.

Claim 26 (New): A method for polishing a semiconductor wafer using a laminated body for polishing of a semiconductor wafer, which comprises a polishing pad for a semiconductor wafer as defined in Claim 18, and a supporting layer laminated on a backside of said polishing pad for a semiconductor wafer, wherein said laminated body has light transmitting properties in a laminated direction, and which comprises a process of detecting a polishing endpoint by the use of an optical endpoint detecting apparatus.

Claim 27 (New): The polishing pad for a semiconductor wafer according to Claim 18,

wherein said polishing pad comprises a fixing layer formed on a backside of at least the substrate for a polishing pad among the substrate for a polishing pad and the light transmitting part for fixing to a polishing apparatus, and

wherein said polishing pad has said through hole at a site corresponding to a light transmitting part of the fixing layer.